

# Contents

<b>Introduction</b>	<b>1</b>
<u>Part I Semiconductor Physics</u>	
<b>Chapter 1 Physics and Properties of Semiconductors—A Review</b>	<b>7</b>
1.1 Introduction, 7	
1.2 Crystal Structure, 8	
1.3 Energy Bands and Energy Gap, 12	
1.4 Carrier Concentration at Thermal Equilibrium, 16	
1.5 Carrier-Transport Phenomena, 28	
1.6 Phonon, Optical, and Thermal Properties, 50	
1.7 Heterojunctions and Nanostructures, 56	
1.8 Basic Equations and Examples, 62	
<u>Part II Device Building Blocks</u>	
<b>Chapter 2 <i>p-n</i> Junctions</b>	<b>79</b>
2.1 Introduction, 79	
2.2 Depletion Region, 80	
2.3 Current-Voltage Characteristics, 90	
2.4 Junction Breakdown, 102	
2.5 Transient Behavior and Noise, 114	
2.6 Terminal Functions, 118	
2.7 Heterojunctions, 124	
<b>Chapter 3 Metal-Semiconductor Contacts</b>	<b>134</b>
3.1 Introduction, 134	
3.2 Formation of Barrier, 135	
3.3 Current Transport Processes, 153	
3.4 Measurement of Barrier Height, 170	
3.5 Device Structures, 181	
3.6 Ohmic Contact, 187	

<b>Chapter 4 Metal-Insulator-Semiconductor Capacitors</b>	<b>197</b>
4.1 Introduction, 197	
4.2 Ideal MIS Capacitor, 198	
4.3 Silicon MOS Capacitor, 213	

### Part III Transistors

<b>Chapter 5 Bipolar Transistors</b>	<b>243</b>
5.1 Introduction, 243	
5.2 Static Characteristics, 244	
5.3 Microwave Characteristics, 262	
5.4 Related Device Structures, 275	
5.5 Heterojunction Bipolar Transistor, 282	

<b>Chapter 6 MOSFETs</b>	<b>293</b>
6.1 Introduction, 293	
6.2 Basic Device Characteristics, 297	
6.3 Nonuniform Doping and Buried-Channel Device, 320	
6.4 Device Scaling and Short-Channel Effects, 328	
6.5 MOSFET Structures, 339	
6.6 Circuit Applications, 347	
6.7 Nonvolatile Memory Devices, 350	
6.8 Single-Electron Transistor, 360	

<b>Chapter 7 JFETs, MESFETs, and MODFETs</b>	<b>374</b>
7.1 Introduction, 374	
7.2 JFET and MESFET, 375	
7.3 MODFET, 401	

### Part IV Negative-Resistance and Power Devices

<b>Chapter 8 Tunnel Devices</b>	<b>417</b>
8.1 Introduction, 417	
8.2 Tunnel Diode, 418	
8.3 Related Tunnel Devices, 435	
8.4 Resonant-Tunneling Diode, 454	

<b>Chapter 9 IMPATT Diodes</b>	<b>466</b>
9.1 Introduction, 466	

- 9.2 Static Characteristics, 467
- 9.3 Dynamic Characteristics, 474
- 9.4 Power and Efficiency, 482
- 9.5 Noise Behavior, 489
- 9.6 Device Design and Performance, 493
- 9.7 BARITT Diode, 497
- 9.8 TUNNETT Diode, 504

## **Chapter 10 Transferred-Electron and Real-Space-Transfer Devices 510**

- 10.1 Introduction, 510
- 10.2 Transferred-Electron Device, 511
- 10.3 Real-Space-Transfer Devices, 536

## **Chapter 11 Thyristors and Power Devices 548**

- 11.1 Introduction, 548
- 11.2 Thyristor Characteristics, 549
- 11.3 Thyristor Variations, 574
- 11.4 Other Power Devices, 582

## Part V Photonic Devices and Sensors

## **Chapter 12 LEDs and Lasers 601**

- 12.1 Introduction, 601
- 12.2 Radiative Transitions, 603
- 12.3 Light-Emitting Diode (LED), 608
- 12.4 Laser Physics, 621
- 12.5 Laser Operating Characteristics, 630
- 12.6 Specialty Lasers, 651

## **Chapter 13 Photodetectors and Solar Cells 663**

- 13.1 Introduction, 663
- 13.2 Photoconductor, 667
- 13.3 Photodiodes, 671
- 13.4 Avalanche Photodiode, 683
- 13.5 Phototransistor, 694
- 13.6 Charge-Coupled Device (CCD), 697
- 13.7 Metal-Semiconductor-Metal Photodetector, 712
- 13.8 Quantum-Well Infrared Photodetector, 716
- 13.9 Solar Cell, 719

<b>Chapter 14 Sensors</b>	<b>743</b>
14.1 Introduction, 743	
14.2 Thermal Sensors, 744	
14.3 Mechanical Sensors, 750	
14.4 Magnetic Sensors, 758	
14.5 Chemical Sensors, 765	
<b>Appendixes</b>	<b>773</b>
A. List of Symbols, 775	
B. International System of Units, 785	
C. Unit Prefixes, 786	
D. Greek Alphabet, 787	
E. Physical Constants, 788	
F. Properties of Important Semiconductors, 789	
G. Properties of Si and GaAs, 790	
H. Properties of $\text{SiO}_2$ and $\text{Si}_3\text{N}_4$ , 791	
<b>Index</b>	<b>793</b>